L Number	Hits	Search Text	DB	Time stamp
48	16	(((((memory adj device) and capacitor) and vertical adj3 transistor) and	USPAT;	2004/09/30 11:44
		select\$7 adj2 transistor) and adjacent near5 lines) and second adj3 lines	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
50	2	fuhrmann-D\$7.in. and trench adj capacitor	USPAT;	2004/09/30 11:46
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
52	3	fuhrmann-D\$7.in. and select\$8 adj transistor	USPAT;	2004/09/30 11:46
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
53	28201	(memory adj device) and capacitor	USPAT;	2004/09/30 11:56
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
54	137	((memory adj device) and capacitor) and zigzag	USPAT;	2004/09/30 11:57
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
55	10	(((memory adj device) and capacitor) and zigzag) and select\$7 adj	USPAT;	2004/09/30 12:21
		transistor	US-PGPUB;	200 17 0 57 50 12 21
			EPO; JPO;	
			DERWENT	
51	2	"20040135190"	USPAT;	2004/09/30 13:21
·	_	20010133170	US-PGPUB;	2004/03/30 13.21
			EPO; JPO;	
			DERWENT	
49	21	fuhrmann-D\$7.in.		2004/09/30 14:08
77	21		USPAT; US-PGPUB;	2004/09/30 14:08
			EPO; JPO;	
			DERWENT	
_	1	US20040022100A1		2004/06/27 18:36
-	1	0320040022100A1	USPAT; US-PGPUB;	2004/00/27 18:30
			EPO; JPO; DERWENT	
_	2	"20040022100"		2004/09/29 17:47
_		20040022100	USPAT;	2004/09/29 17:47
			US-PGPUB;	
		,	EPO; JPO; DERWENT	
	172710	mamanu adi daviaa		2004/00/20 17.49
-	172710	memory adj device	USPAT;	2004/09/29 17:48
			US-PGPUB;	ĺ
			EPO; JPO;	
-	1	2004-110827.NRAN. and capacitor	DERWENT	2004/00/20 17:40
	1	2004-110027.INICAIN. and capacitor	USPAT;	2004/09/29 17:48
			US-PGPUB;	
			EPO; JPO;	
	500	((mamony adi davias) and consolted) and control of 12 42 4 5 5	DERWENT	2004/00/20 := :0
-	590	((memory adj device) and capacitor) and vertical adj3 transistor	USPAT;	2004/09/29 17:49
			US-PGPUB;	
			EPO; JPO;	
	00		DERWENT	
-	98	(((memory adj device) and capacitor) and vertical adj3 transistor) and	USPAT;	2004/09/29 17:50
		select\$7 adj2 transistor	US-PGPUB;	
			ЕРО; ЈРО;	
-	40		DERWENT	
	48	((((memory adj device) and capacitor) and vertical adj3 transistor) and	USPAT;	2004/09/29 17:50
		select\$7 adj2 transistor) and adjacent near5 lines	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
	10	(((((memory adj device) and capacitor) and vertical adj3 transistor) and	USPAT;	2004/09/29 17:51
		select\$7 adj2 transistor) and adjacent near5 lines) and first adj2 lines	US-PGPUB;	
			EPO; JPO;	
			DERWENT	

-	8	((((((memory adj device) and capacitor) and vertical adj3 transistor) and	USPAT;	2004/09/29 17:54
		select\$7 adj2 transistor) and adjacent near5 lines) and first adj2 lines) and	US-PGPUB;	
		((((((memory adj device) and capacitor) and vertical adj3 transistor) and	EPO; JPO;	
		select\$7 adj2 transistor) and adjacent near5 lines) and second adj3 lines)	DERWENT	
-	6	(("5,691,934") or ("5,736,761") or ("6,118,683")).PN.	USPAT;	2004/09/29 17:56
			US-PGPUB;	
	ļ		EPO; JPO;	
	į		DERWENT	
-	6	6,448,600	USPAT;	2004/09/29 17:55
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	3	5,691,934	USPAT;	2004/09/29 17:56
	ł		US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT	
-	10	5,736,761	USPAT;	2004/09/29 17:56
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	3	6,118,683	USPAT;	2004/09/29 17:56
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	22	6,448,600 or 5,691,934 or 5,736,761 or 6,118,683	USPAT;	2004/09/29 17:57
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	